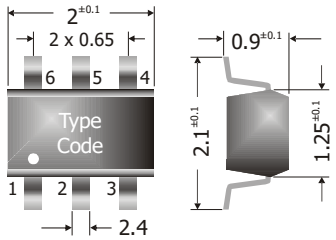
Diotec Semiconductor

BAS70DW, BAS70ADW, BAS70CDW, BAS70SDW
SMD Small Signal Diode Arrays
SMD Kleinsignal-Dioden-Arrays

I_{FAV} = 70 mA **V_{RRM} = 70 V**
V_{F1} < 0.410 V **I_{FSM} = 100 mA**
T_{jmax} = 125°C

Version 2018-09-19

SOT-363



Dimensions - Maße [mm]

Typical Applications
Signal processing, High-speed switching, Polarity protection
Commercial grade
Suffix -Q: AEC-Q101 compliant [1])
Suffix -AQ: in AEC-Q101 qualification [1])

Typische Anwendungen
Signalverarbeitung, Schnelles Schalten, Verpolschutz
Standardausführung
Suffix -Q: AEC-Q101 konform [1])
Suffix -AQ: in AEC-Q101 Qualifikation [1])

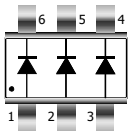
Features
Very low t_{rr}, C_j and I_R
Compliant to RoHS, REACH, Conflict Minerals [1])

Besonderheiten
Sehr niedriges t_{rr}, C_j und I_R
Konform zu RoHS, REACH, Konfliktmineralien [1])

Mechanical Data [1])		**Mechanische Daten [1])**
Taped and reeled	3000 / 7"	Gegurtet auf Rolle
Weight approx.	0.01 g	Gewicht ca.
Case material	UL 94V-0	Gehäusematerial
Solder & assembly conditions	260°C/10s MSL = 1	Löt- und Einbaubedingungen

BAS70DW

3 Single Diodes

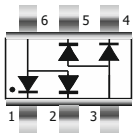


Type Code 7A

1 = A1, 2 = A2, 3 = A3
4 = C3, 5 = C2, 6 = C1

BAS70ADW

2 x 2 Common Anode

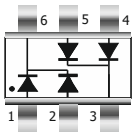


Type Code 7B

1 = C1, 2 = C2, 3 = A3/A4
4 = C3, 5 = C4, 6 = A1/A2

BAS70CDW

2 x 2 Common Cathode

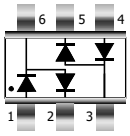


Type Code 7C

1 = A1, 2 = A2, 3 = C3/C4
4 = A3, 5 = A4, 6 = C1/C2

BAS70SDW

4 in Bridge Config-uration



Type Code 7D

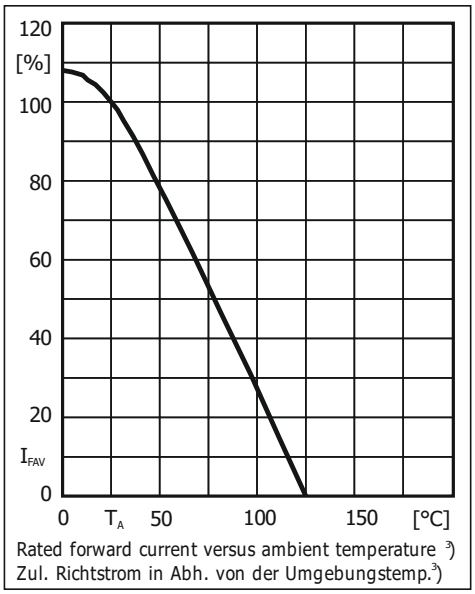
1 = A1, 2 = C2, 3 = A4/C3
4 = A3, 5 = C4, 6 = A2/C1

Maximum ratings [2]) **Grenzwerte [2])**			
Total power dissipation (per package) – Gesamtverlustleistung (pro Gehäuse)		P_{tot}	200 mW [3])
Max. average forward current – Dauergrenzstrom	DC	I_{FAV}	70 mA [3])
Non repetitive peak forward surge current – Stoßstrom-Grenzwert	$t_p \le 1$ s	I_{FSM}	100 mA
Repetitive peak reverse voltage – Periodische Spitzensperrspannung		V_{RRM}	70 V
Reverse voltage – Sperrspannung	DC	V_R	70 V
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_S	-55…+125°C -55…+125°C

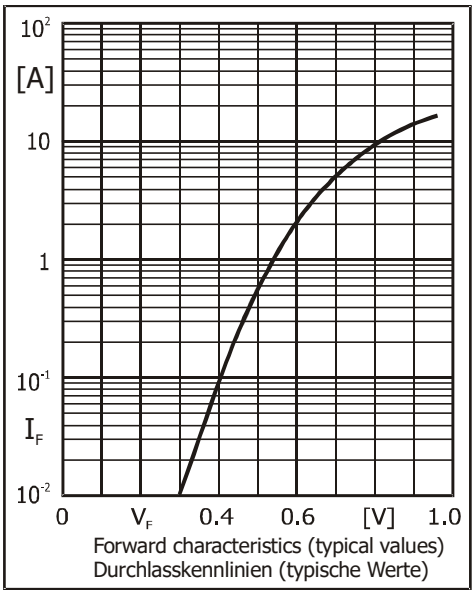
1 Please note the detailed information on our website or at the beginning of the data book
Bitte beachten Sie die detaillierten Hinweise auf unserer Internetseite bzw. am Anfang des Datenbuches
2 T_A = 25°C and per diode, unless otherwise specified – T_A = 25°C und pro Diode, wenn nicht anders angegeben
3 Mounted on P.C. board with 3 mm² copper pad per terminal – Montage auf Leiterplatte mit 3 mm² Lötpad je Anschluss

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Characteristics [1])			**Kennwerte [1])**
Forward voltage Durchlass-Spannung [2])	T_j = 25°C	I_F = 1 mA 15 mA	V_F	< 410 mV < 1000 mV
Leakage current Sperrstrom [2])	T_j = 25°C	V_R = 50 V	I_R	< 100 nA
Junction capacitance Sperrschichtkapazität	V_R = 0 V, f = 1 MHz		C_T	typ. 2 pF
Reverse recovery time Sperrverzug	I_F = 10 mA über/through I_R = 10 mA bis/to I_R = 1 mA		t_{rr}	< 5 ns
Thermal resistance junction to ambient (per package) Wärmewiderstand Sperrschicht – Umgebung (per Gehäuse)			R_{thA}	< 500 K/W [3])



Rated forward current versus ambient temperature [3])
Zul. Richtstrom in Abh. von der Umgebungstemp.[3])



Forward characteristics (typical values)
Durchlasskennlinien (typische Werte)

Disclaimer: See data book page 2 or website
Haftungssauschluss: Siehe Datenbuch Seite 2 oder Internet

1 Valid per diode, unless otherwise specified
Gültig pro Diode, wenn nicht anders angegeben
2 Tested with pulses t_p = 300 µs, duty cycle ≤ 2%
Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%
3 Mounted on 3 mm² copper pads per terminal
Montage auf 3 mm² Kupferbelag (Lötpads) je Anschluss

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